



Insulator-metal transition in the doped $3d^1$ transition-metal oxides: a combined LDA+DMFT study

L. CRACO

Institut für Theoretische Physik • Universität zu Köln

Motivation

To analyse the Mott-Hubbard insulator-metal transition (IMT) in $3d^1$ TM-oxides LaTiO_3 and TiOCl using the *ab initio* LDA+DMFT method. The calculation is performed using real crystal structure and realistic parameters (U, U', J_H) as input.

Model and Method of Solution

Our aim is to provide a multi-orbital correlated *ab initio* description of real materials based on

Model Hamiltonian

$$H = H_{\text{LDA}} + H_U,$$

where

$$H_{\text{LDA}} = \sum_{\mathbf{k}, \alpha, \beta} \epsilon_{\alpha\beta}(\mathbf{k}) c_{\mathbf{k}\alpha\sigma}^\dagger c_{\mathbf{k}\beta\sigma} + \sum_{i\alpha\sigma} \epsilon_{i\alpha\sigma}^0 n_{i\alpha\sigma},$$

$$\epsilon_{i\alpha\sigma}^0 = \epsilon_{i\alpha\sigma} - U(n_{i\alpha\bar{\sigma}} - \frac{1}{2}) + \frac{1}{2} J_H (n_{i\alpha\sigma} - 1), \text{ and}$$

$$H_U = U \sum_{i\alpha} n_{i\alpha\uparrow} n_{i\alpha\downarrow} + U' \sum_{i\alpha, \beta\sigma'} n_{i\alpha\sigma} n_{i\beta\sigma'}.$$

α, β are orbital indexes; $U' = U - 2J_H$.

Multi-Orbital LDA+DMFT(IPT)

The LDA+DMFT solution involves (i) replacing the lattice model by a multi-orbital Anderson impurity model, and (ii) a self-consistency condition requiring the impurity propagator to be equal to the local (k -averaged) GF of the lattice

$$G_\alpha(\omega) = \frac{1}{N} \sum_{\mathbf{k}} \frac{1}{\omega + \mu - \Sigma_\alpha(\omega) - \epsilon_{\mathbf{k}\alpha}}.$$

Local self-energies \Rightarrow multi-orbital (extended) IPT

$$\Sigma_\alpha(\omega) = \frac{\sum_\gamma A_{\alpha\gamma} \Sigma_{\alpha\gamma}^{(2)}(\omega)}{1 - \sum_\gamma B_{\alpha\gamma} \Sigma_{\alpha\gamma}^{(2)}(\omega)}.$$

where,

$$\Sigma_{\alpha\gamma}^{(2)}(i\omega) = N_{\alpha\gamma} \frac{U_{\alpha\gamma}^2}{\beta^2} \sum_{nm} G_\alpha^0(i\omega_n) G_\gamma^0(i\omega_m) G_\alpha^0(i\omega_n + i\omega_m - i\omega),$$

$G_\alpha^0(\omega) = \frac{1}{\omega + \mu - \Delta_\alpha(\omega)}$ is the bath propagator,

$$A_{\alpha\gamma} = \frac{n_\alpha(1-2n_\alpha + D_{\alpha\gamma})}{n_\alpha^2(1-n_\alpha^2)}, \quad B_{\alpha\gamma} = \frac{(1-2n_\alpha)U_{\alpha\gamma} + \mu - \mu_\alpha}{2U_{\alpha\gamma} n_\alpha^2(1-n_\alpha^2)}.$$

n_α, n_α^0 are particle numbers determined from G_α and G_α^0 .

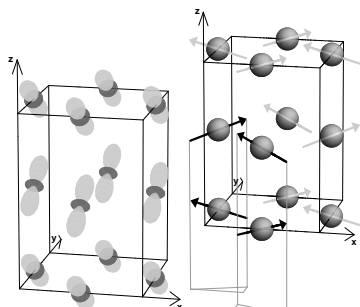
The interorbital correlation function $D_{\alpha\gamma}[n] = \langle n_\alpha n_\gamma \rangle$ is calculated from

$$\langle n_\alpha n_\gamma \rangle = \langle n_\alpha \rangle \langle n_\gamma \rangle - \frac{1}{U_{\alpha\gamma}} \int_{-\infty}^{+\infty} f(\omega) \text{Im}[\Sigma_\alpha(\omega) G_\alpha(\omega)] d\omega.$$

We have used this or similar techniques to study:

CMR manganites, LiV_2O_4 , V_2O_3 , VO_2 , CrO_2 , $\text{Ga}_{1-x}\text{Mn}_x\text{As}$, LaTiO_3 , TiOCl , and ...

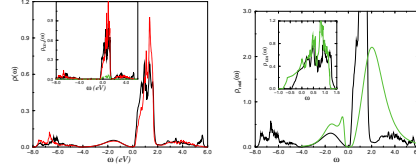
LaTiO_3 : orbital and magnetic order



see, R. Schmitz et al., cond-mat/0407524.

Mott transition in $\text{La}_{1-x}\text{Sr}_x\text{TiO}_{3+y/2}$

Motivation: to demonstrate the nature of the Mott insulating state and the doping-induced insulator-metal in this system.

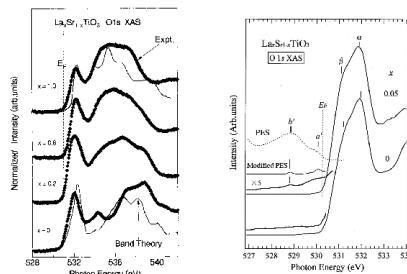


Left: LDA DOS (inset) and LDA+DMFT (orbital resolved) DOS. Right: The inset shows the LDA DOS for the non-degenerate ground-state orbital, ours (black) and downfolded (green). The main panel shows the Total LDA+DMFT DOS for undoped LaTiO_3 , using in the LDA+DMFT(IPT) [$U = 6 \text{ eV}, J_H = 1 \text{ eV}, T = 0$] and in LDA+DMFT(QMC) [$U = 5 \text{ eV}, J_H = 0.64 \text{ eV}, T = 770 \text{ K}$], by E. Pavarini et al., PRL 92, 176403 (2004).

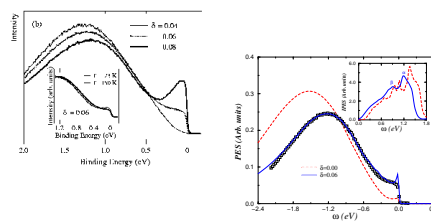
Notes

- i) Our solution support ferro-orbital order in the insulating state and a carrier driven (continuous filling induced) IMT in LaTiO_3 .
- ii) Our results imply that LaTiO_3 can be described as a Mott-Hubbard system without orbital (liquid) degeneracy.

XAS and PES spectra



Left: A. Fujimori et al. PRB 46 9841 (1992); Right: T. Higuchi et al. PRB 61 12860 (2000).



Left: Valence-band photoemission in the low doping regime by T. Yoshida et al. EPL 59, 258 (2002). Right: PES and IPES (inset) spectra for both, pure (dashed) and Sr-doped (solid) LaTiO_3 .

Note

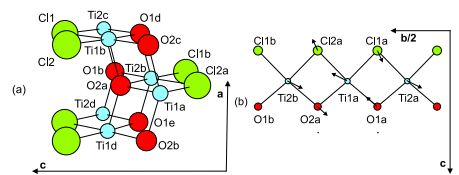
Note the excellent quantitative agreement with photoemission data for $\delta = x = 0.06$. We also resolve the α, β peaks in the XAS spectrum (right inset).

For more details see L. Craco, M. S. Laad, S. Leoni, and E. Müller-Hartmann, PRB 70, 195116 (2004).

Concluding remark

LDA+DMFT (IPT+CPA) scheme gives semiquantitative consistency with a range of experimental observations for LaTiO_3 .

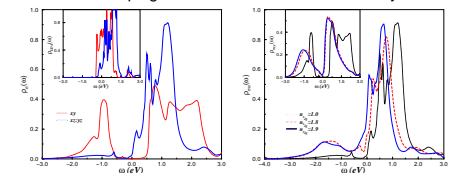
TiOCl crystal structure



Crystal structure of TiOCl : (a) Perspective view of one layer. (b) A chain of Ti atoms. The displacements in the superstructure are given by arrows. Figures taken from M. Shaz et al., cond-mat/0503203.

Spectral properties of TiOCl

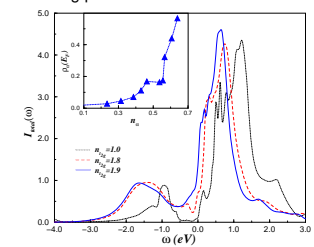
Motivation: to study the nature of the Mott-Hubbard insulating state and the doping-induced insulator-metal in this system.



Left: LDA+DMFT(IPT) and LDA (inset) partial DOS. Red line denotes the DOS for the non-degenerate ground-state (xy) orbital. Blue line denotes the DOS for the higher (two-fold degenerate) lying $\alpha \equiv xz \equiv yz$ orbitals. Right: t_{2g} partial DOS for the $3d_a$ and $3d_{xy}$ (inset) orbitals for $U = 3 \text{ eV}$ and $J_H = 1 \text{ eV}$ and different values of the total electron number.

Notes

- i) The charge gap shows the Mott-Hubbard character of the insulator. DMFT gives non-trivial renormalization of the crystal field splitting, $\Delta_{2g} = \epsilon_{xy} - \epsilon_\alpha = 0.12 \text{ eV}$ ($\Delta_{LD} = -0.45 \text{ eV}$).
- ii) Doping TiOCl with electrons induces a nearly first-order IMT with rapid change in the carrier density around $n_{t_{2g}} = 1.9$. Notice that *only* the d_a bands show metallic behaviour; the d_{xy} DOS still represents almost insulating behaviour.
- iii) For $n_{t_{2g}} = 1.9$, the renormalized value of $\Delta_{2g}^M = -0.011 \Rightarrow$ implying melting of the (spin) dimerization observed in the insulating phase.



Total spectra for different values of the total electron number. Inset shows the d_{xy} DOS at E_F for different values of the d_{xy} orbital occupation.

We believe that the above results are the first demonstration of the possibility of driving a Mott transition in TiOCl by electron doping in a realistic scenario.

For more details see L. Craco, M. S. Laad, and E. Müller-Hartmann, cond-mat/0410472.

Concluding remark

Many-body electron-electron interactions introduces non-trivial effects stemming from the dynamical nature of electronic systems, leading to large transfer of spectral weight across large energy scales in response to small changes in the bare electronic structure. This type of response is at the heart of the anomalous responses of correlated systems.